TO SEPARATE, HOLD TOP AND BOTTOM EDGES, SNAP-APART AND DISCARD CARBON

FORM PTO-892 (REV. 2-92) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	SERIAL NO.	GROUP ART UNIT	ATTACHMENT TO PAPER NUMBER
NOTICE OF REFERENCES CITED	APPLICANT(S) Tsang et al.	2309	

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*		DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE
	A	5 2 1 5 4 7 2	5/25/93	Eidson et al	257	350	
	B	4 9 1 4 9 2 9	4/3/90	Blanchard	257	373	
	C						
	D						
	E						
	F						
	G						
	H						
	I						
	J						
	K						

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*		DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUB-CLASS	PERTINENT SHTS. DWG.	PERTINENT PP. SPEC.
	L	3 1 [illegible] 9 7 7 5	5/91	Japan	Sakamoto	257	372		
	M								
	N								
	O								
	P								
	Q								

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER	DATE	

* A copy of this reference is not being furnished with this office action.
(See Manual of Patent Examining Procedure, section 707.05 (a).)

FORM PTO-892 (REV. 3-78) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

NOTICE OF REFERENCES CITED

SERIAL NO.	GROUP ART UNIT	ATTACHMENT TO PAPER NUMBER

APPLICANT(S)
D Tsang et al

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*	A	5,108,427	8/92	Tsang et al	437	40	
*	B	4,558,712	5/86	Baliga	437	6	
*	C	5,089,434	2/92	Hillenius	437	~~35~~ 41	
*	D	5,017,522	5/91	Morgan et al	437	40	
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*	F	5,108,937	4/92	Tsang et al	"	"	
*	G	4,711,335	12/87	Bulat et al	437	6	
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*		DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUB-CLASS	PERTINENT SHTS. DWG	PERTINENT PP. SPEC.
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EXAMINER | DATE

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(See Manual of Patent Examining Procedure, section 707.05(a).)